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TECHNOLOGY CENTER R3700

PATENT  
MIC04 P-113



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Imad Mahawili, Ph.D  
Serial No. : 10/074,287  
Filing Date : February 12, 2002  
Group : 2835  
Confirmation No. : 4900  
For : ULTRA RAPID THERMAL PROCESSING  
CHAMBER AND METHOD OF USE

Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

PRELIMINARY AMENDMENT

Prior to examination, Applicant wishes to amend his application as follows:

IN THE CLAIMS:

Please add the following new claims:

51. (New) The semiconductor processing apparatus according to Claim 4, wherein said second energy source comprises at least one lamp having a normal operating condition generating a normal output spectrum and a normal peak operating voltage, said lamp adapted to apply a high energy voltage to the device side, said high energy voltage exceeding said normal peak operating voltage, and when applying said high energy voltage said lamp generating a shifted output energy spectrum whereby said lamp generates a peak energy voltage at a shorter wavelength than said normal peak operating voltage.

52. (New) The semiconductor processing apparatus according to Claim 51, wherein said shifted output energy spectrum generates an output energy over a range of about 0.2 microns to 0.9 microns.

53. (New) The semiconductor processing apparatus according to Claim 51, wherein said lamp comprises a tungsten halogen lamp.